

# GT15J321

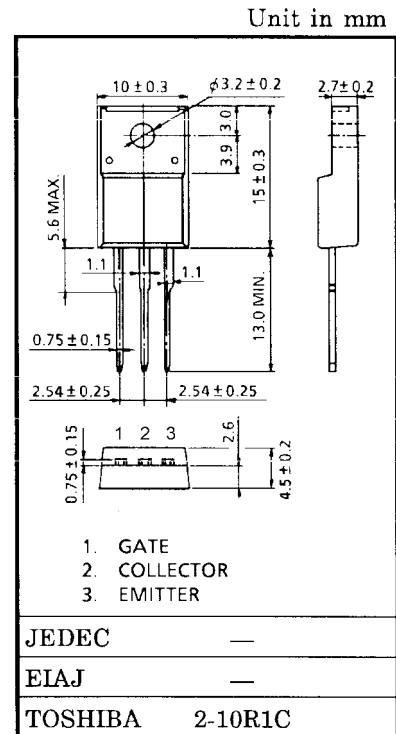
High Power Switching Applications

Fast Switching Applications

- The 4th generation
- FS (fast switching)
- Enhancement-mode
- High speed:  $t_f = 0.03 \mu s$  (typ.)
- Low saturation Voltage:  $V_{CE(sat)} = 1.90 V$  (typ.)
- FRD included between emitter and collector.

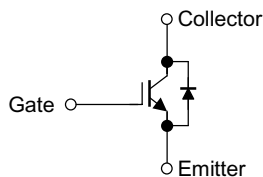
### Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics		Symbol	Rating	Unit
Collector-emitter voltage		$V_{CES}$	600	V
Gate-emitter voltage		$V_{GES}$	$\pm 20$	V
Collector current	DC	$I_C$	15	A
	1 ms	$I_{CP}$	30	
Emitter-collector forward current	DC	$I_F$	15	A
	1 ms	$I_{FM}$	30	
Collector power dissipation ( $T_c = 25^\circ C$ )		$P_C$	30	W
Junction temperature		$T_j$	150	$^\circ C$
Storage temperature range		$T_{stg}$	-55~150	$^\circ C$



Weight: 1.7 g

### Equivalent Circuit



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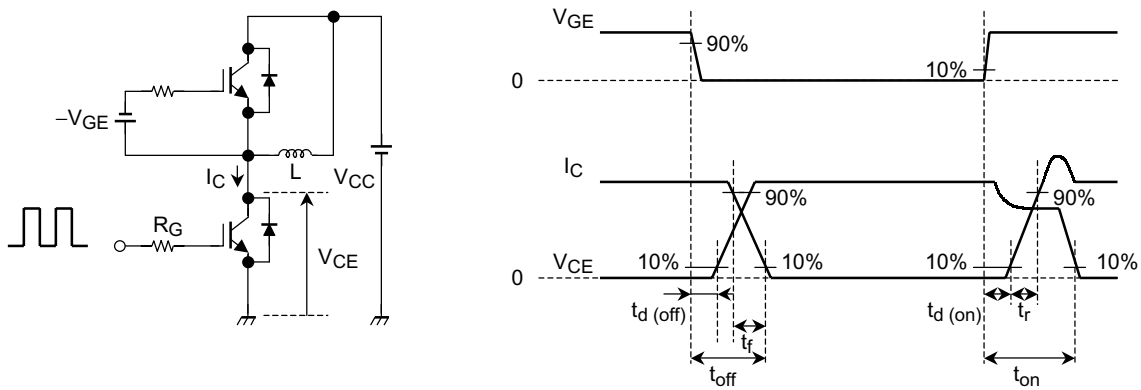
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## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GES}$	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0$	—	—	$\pm 500$	nA
Collector cut-off current		$I_{CES}$	$V_{CE} = 600\text{ V}, V_{GE} = 0$	—	—	1.0	mA
Gate-emitter cut-off voltage		$V_{GE (OFF)}$	$I_C = 1.5\text{ mA}, V_{CE} = 5\text{ V}$	3.5	—	6.5	V
Collector-emitter saturation voltage		$V_{CE (sat)}$	$I_C = 15\text{ A}, V_{GE} = 15\text{ V}$	—	1.90	2.45	V
Input capacitance		$C_{ies}$	$V_{CE} = 20\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$	—	2300	—	pF
Switching time	Rise time	$t_r$	Inductive Load $V_{CC} = 300\text{ V}, I_C = 15\text{ A}$ $V_{GG} = 15\text{ V}, R_G = 43\ \Omega$  (Note 1)	—	0.04	—	$\mu\text{s}$
	Turn-on time	$t_{on}$		—	0.17	—	
	Fall time	$t_f$		—	0.03	0.15	
	Turn-off time	$t_{off}$		—	0.34	—	
Peak forward voltage		$V_F$	$I_F = 15\text{ A}, V_{GE} = 0$	—	—	2.0	V
Reverse recovery time		$t_{rr}$	$I_F = 15\text{ A}, di/dt = -100\text{ A}/\mu\text{s}$	—	—	200	ns
Thermal resistance (IGBT)		$R_{th (j-c)}$	—	—	—	4.16	°C/W
Thermal resistance (Diode)		$R_{th (j-c)}$	—	—	—	4.63	°C/W

Note 1: Switching time measurement circuit and input/output waveforms



Note 2: Switching loss measurement waveforms

